

#### ABSTRACT OF THE DISCLOSURE

A semiconductor device for charge-up damage evaluation and an evaluation method for the same are provided which permit to detect charge-up damage caused by static electricity. There are provided a silicon substrate 9, a first insulation film 10 formed on the silicon substrate 9, a first conductive layer 6 formed on the first insulation film 10 and connected to the silicon substrate 9, a second insulation film 11 formed on the first conductive layer 6, a second conductive layer 8 formed on the second insulation film 11 and serving as an antenna, and a third insulation film 12 formed on the second conductive layer 8.